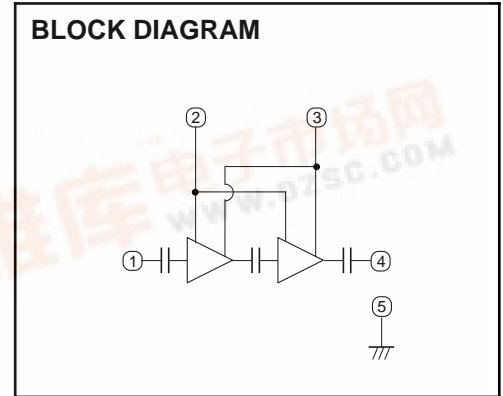
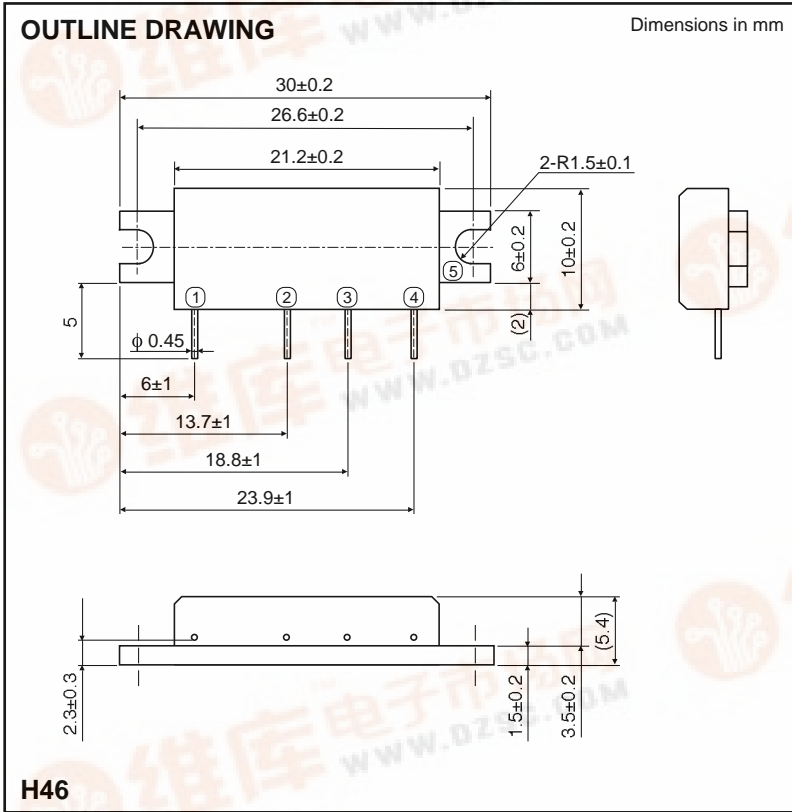


MITSUBISHI RF POWER MODULE

M68710TL

SILICON MOS FET POWER AMPLIFIER, 330-360MHz, 2W, FM PORTABLE RADIO



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Ratings | Unit |
|---------|----------------------------|--------------------------------|-------------|------|
| VDD | Supply voltage | VGG 3.5V, ZG=ZL=50 | 9 | V |
| VGG | Gate bias voltage | | 4 | V |
| Pin | Input power | f=330-360MHz, ZG=ZL=50 | 30 | mW |
| Po | Output power | f=330-360MHz, VDD 9V, ZG=ZL=50 | 3 | W |
| Tc (OP) | Operation case temperature | f=330-360MHz, VDD 9V, ZG=ZL=50 | -30 to +110 | °C |
| Tstg | Storage temperature | | -40 to +110 | °C |

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50 unless otherwise noted)

| Symbol | Parameter | Test conditions | Limits | | Unit | |
|--------|---------------------|--|------------------------------|-----|------|-----|
| | | | Min | Max | | |
| f | Frequency range | | 330 | 360 | MHz | |
| Po | Output power | VDD=6V, VGG=3.5V, Pin=20mW | 2 | | W | |
| η | Total efficiency | | 40 | | % | |
| 2fo | 2nd. harmonic | | | -25 | | dBc |
| in | Input VSWR | | | 4 | | - |
| - | Stability | ZG=50, VDD=4-8V, Load VSWR<4:1 | No parasitic oscillation | | - | |
| - | Load VSWR tolerance | VDD=9V, Pin=20mW, Po=2W (VGG adjust), ZL=20:1 | No degradation or destroy | | - | |

Note. Above parameters, ratings, limits and test conditions are subject to change.

